

## 30V N-Channel Mosfet

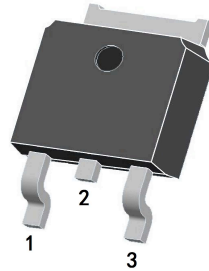
### FEATURES

- $R_{DS(ON)} < 3m\Omega @ V_{GS} = 10V$
- $R_{DS(ON)} < 6m\Omega @ V_{GS} = 4.5V$

### APPLICATIONS

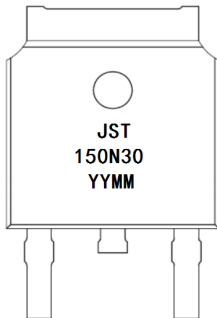
- Load Switch
- PWM Application
- Power management

### TO-252-2L



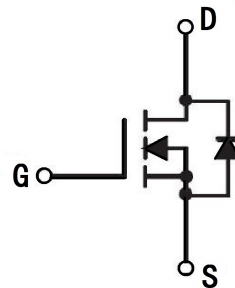
- 1: G
- 2: D
- 3: S

### MARKING



YYMM:Date Code(year&month)

### N-CHANNEL MOSFET



Maximum ratings ( $T_C=25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Max.	Units	
$V_{DSS}$	Drain-Source Voltage	30	V	
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	V	
$I_D$	Continuous Drain Current	$T_C = 25^\circ\text{C}$	150	A
		$T_C = 100^\circ\text{C}$	100	A
$I_{DM}$	Pulsed Drain Current <sup>note1</sup>	400	A	
$E_{AS}$	Single Pulsed Avalanche Energy <sup>note2</sup>	650	mJ	
$P_D$	Power Dissipation	$T_C = 25^\circ\text{C}$	110	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.36	$^\circ\text{C}/\text{W}$	
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +175	$^\circ\text{C}$	

## Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	30	-	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =30V, V <sub>GS</sub> = 0V,	-	-	1.0	μA
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±20V	-	-	±100	nA
<b>On Characteristics</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =250μA	1.0	1.6	3.0	V
R <sub>DS(on)</sub>	Static Drain-Source on-Resistance <small>note3</small>	V <sub>GS</sub> =10V, I <sub>D</sub> =30A	-	2.5	3.0	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A	-	4.2	6.0	mΩ
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =10A	-	28	-	S
<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f = 1.0MHz	-	3400	-	pF
C <sub>oss</sub>	Output Capacitance		-	356	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		-	308	-	pF
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =15V, I <sub>D</sub> =30A, V <sub>GS</sub> =10V	-	70	-	nC
Q <sub>gs</sub>	Gate-Source Charge		-	12	-	nC
Q <sub>gd</sub>	Gate-Drain("Miller") Charge		-	16.3	-	nC
<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DS</sub> =15V, I <sub>D</sub> =60A, R <sub>GEN</sub> =1.8Ω, V <sub>GS</sub> =4.5V	-	11	-	ns
t <sub>r</sub>	Turn-on Rise Time		-	120	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time		-	25	-	ns
t <sub>f</sub>	Turn-off Fall Time		-	60	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current		-	-	150	A
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	400	A
V <sub>SD</sub>	Drain to Source Diode Forward Voltage	V <sub>GS</sub> = 0V, I <sub>S</sub> =20A	-	-	1.2	V
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =60A, dI/dt=100A/μs	-	56	-	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge		-	110	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: T<sub>j</sub>=25°C, V<sub>DD</sub>=30V, V<sub>G</sub>=10V, L=0.5mH, R<sub>g</sub>=25Ω

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

Typical Performance Characteristics

Figure 1: Output Characteristics

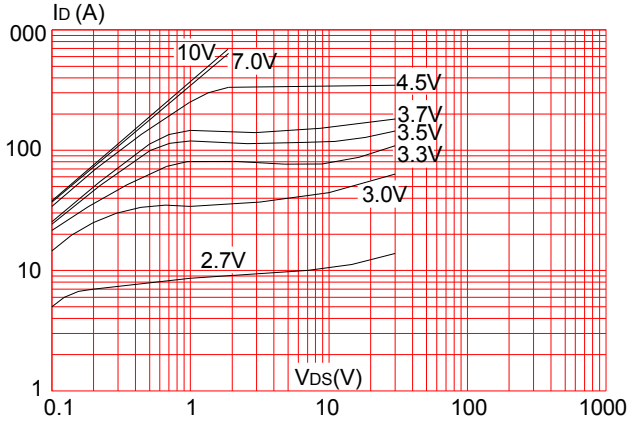


Figure 2: Typical Transfer Characteristics

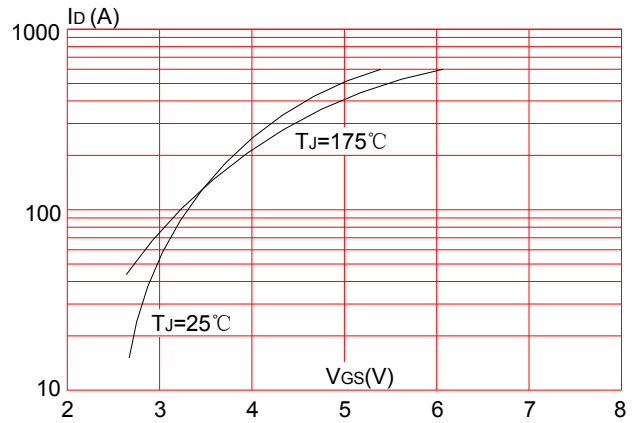


Figure 3: On-resistance vs. Drain Current

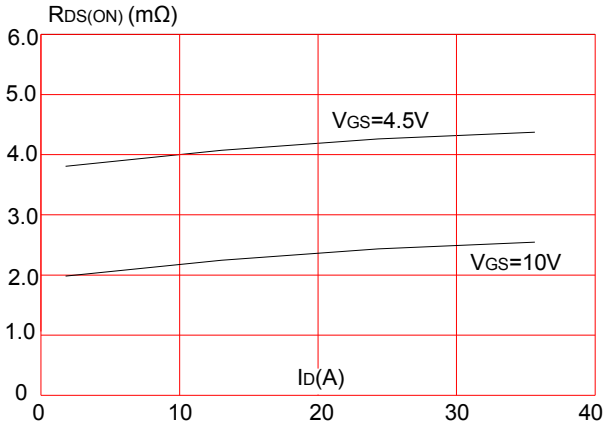


Figure 4: Body Diode Characteristics

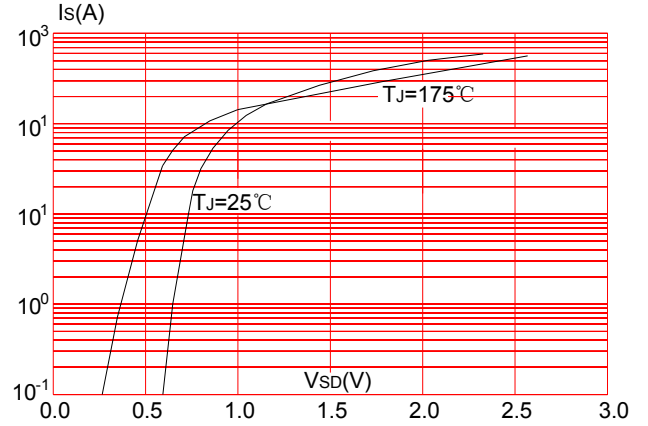


Figure 5: Gate Charge Characteristics

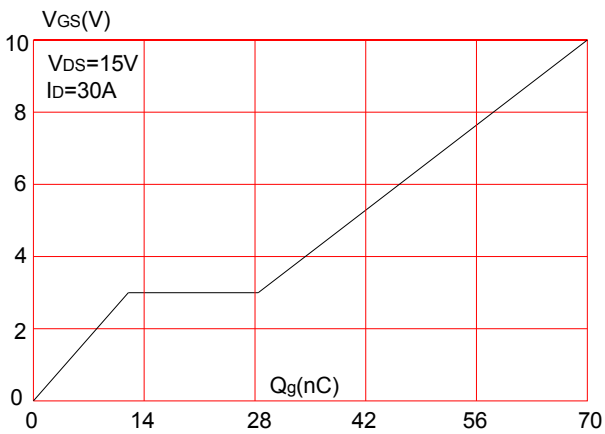
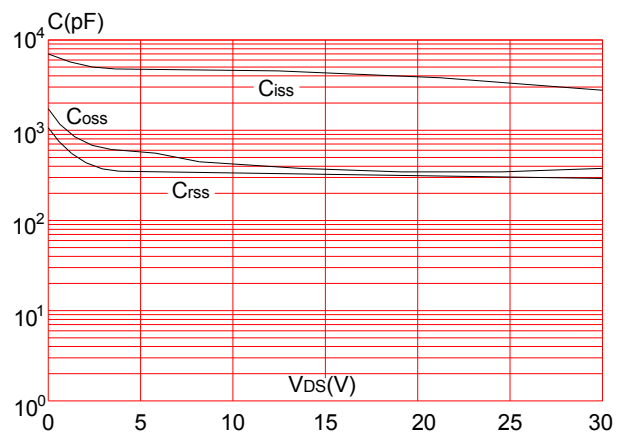
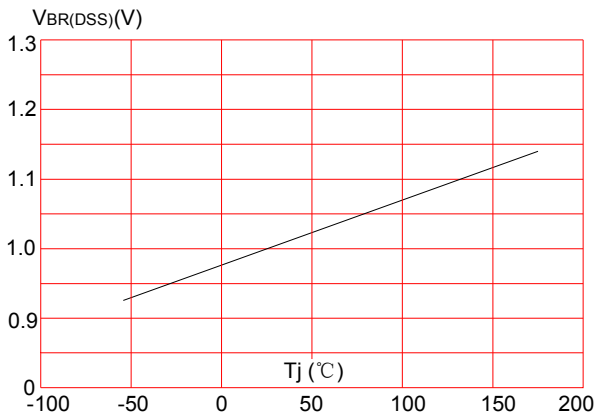


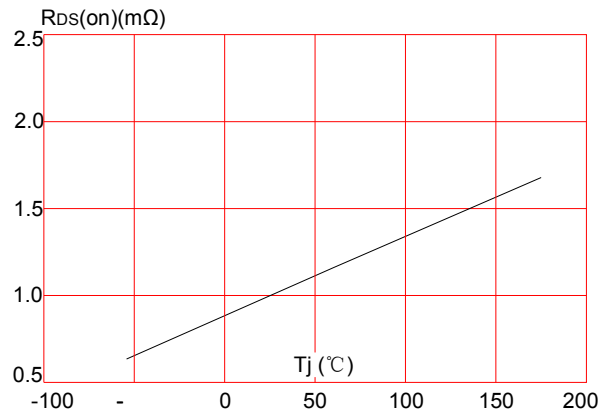
Figure 6: Capacitance Characteristics



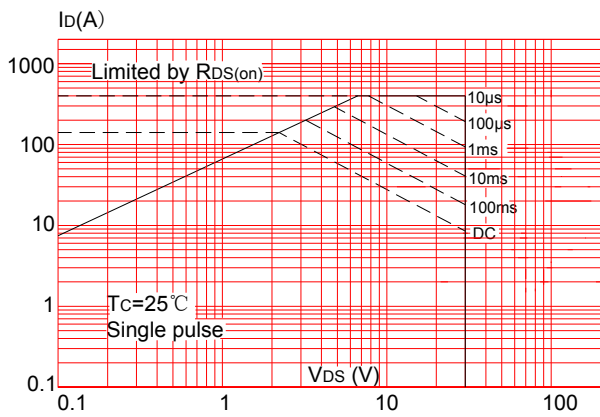
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



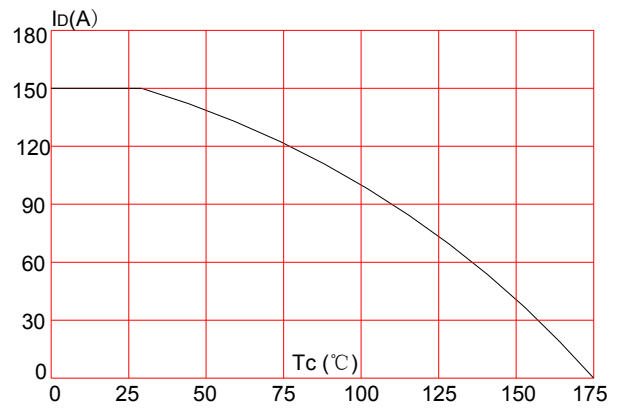
**Figure 8:** Normalized on Resistance vs. Junction Temperature



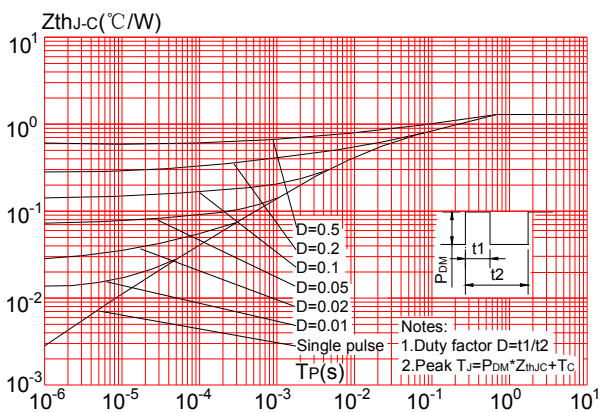
**Figure 9:** Maximum Safe Operating Area



**Figure 10:** Maximum Continuous Drain Current vs. Case Temperature



**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Case



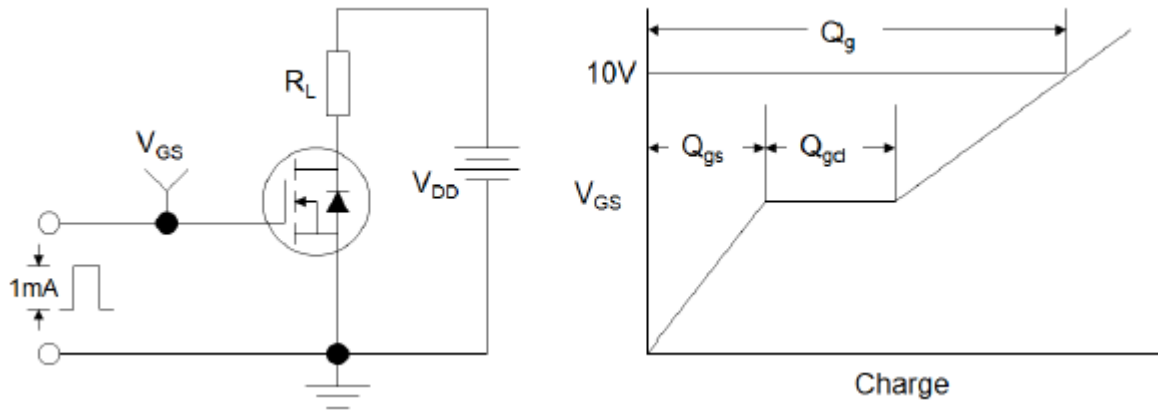


Figure1:Gate Charge Test Circuit & Waveform

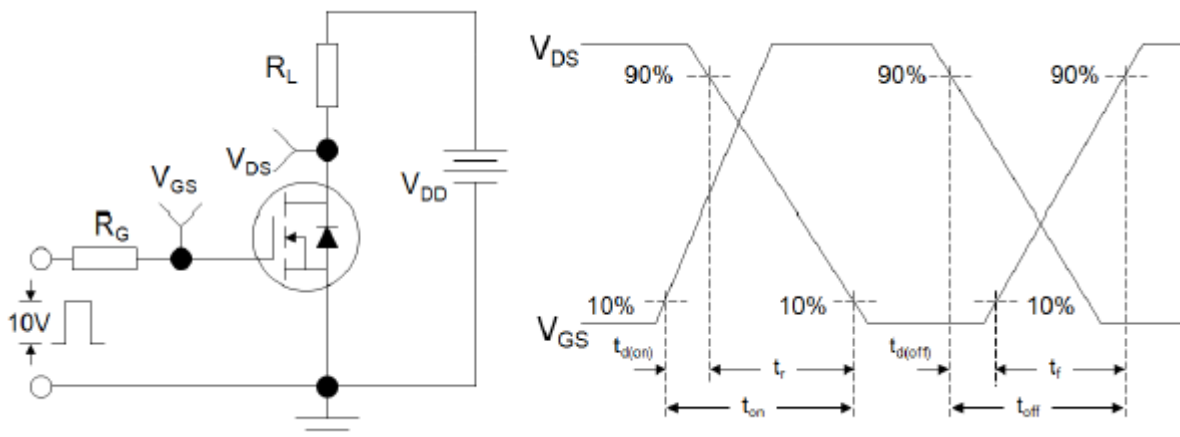


Figure 2: Resistive Switching Test Circuit & Waveforms

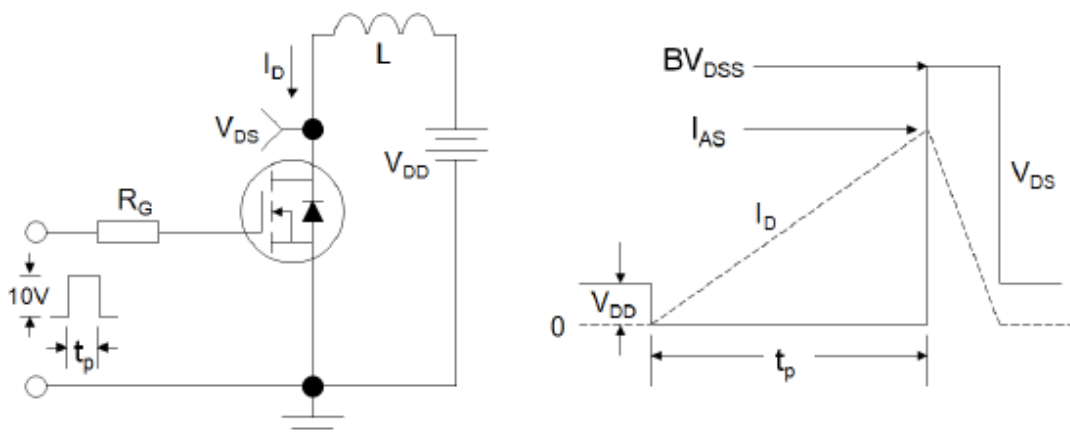


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

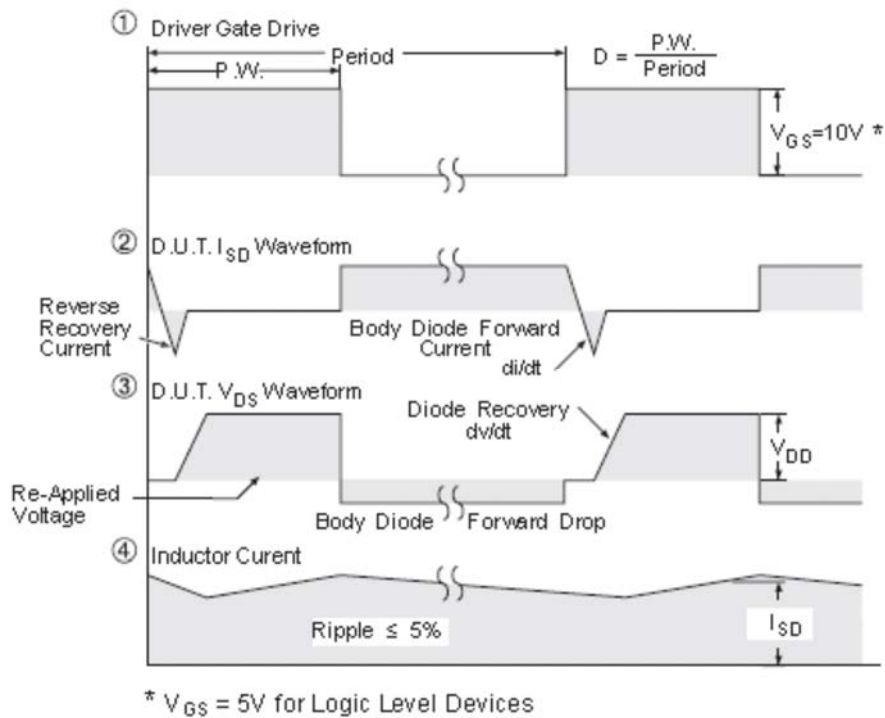
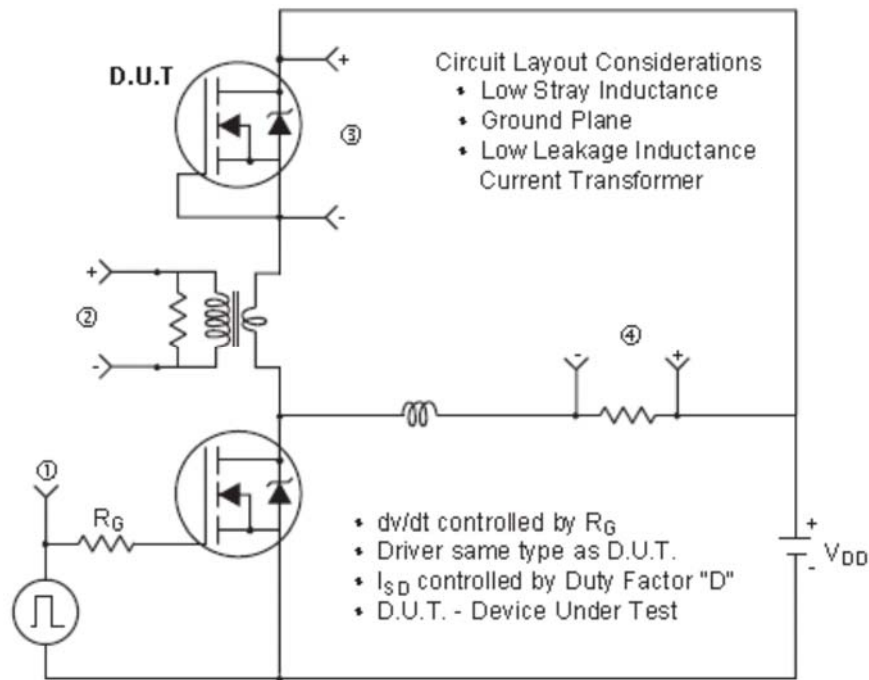
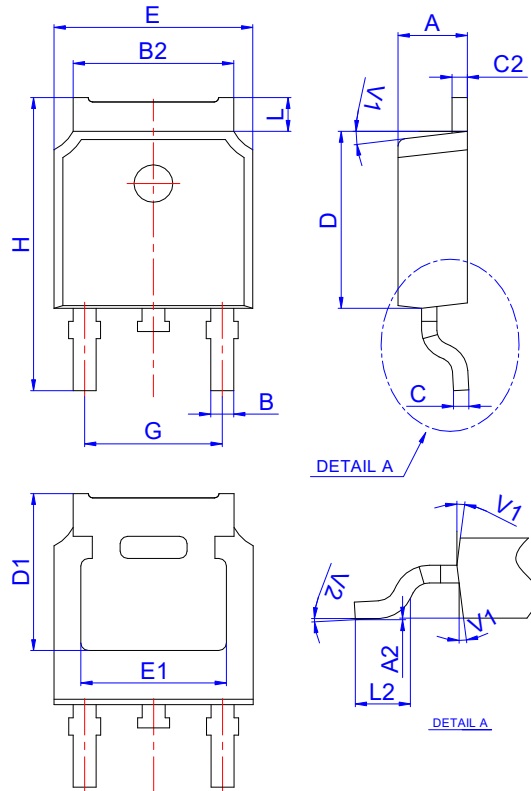


Figure 4: Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms (For N-channel)

## TO-252 PACKAGE OUTLINE DRAWING



Symbols	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°